

Title (en)

HIGHLY-INTEGRATED SEMICONDUCTOR MEMORY AND PROCESS FOR PREPARATION OF THE MEMORY

Title (de)

HOCHINTEGRIERTER HALBLEITERSPEICHER UND VERFAHREN ZUR HERSTELLUNG DES HALBLEITERSPEICHERS

Title (fr)

MEMOIRE A SEMI-CONDUCTEUR HAUTEMENT INTEGREE ET PROCEDE DE FABRICATION DE CETTE MEMOIRE

Publication

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Application

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Abstract (en)

[origin: WO9725744A1] The invention concerns a highly-integrated semiconductor memory with an EPROM cell in the form of a column with a floating gate and a control gate and a process for the preparation of the same. The EPROM cell is so thinly built that it is completely depleted. The control gate of the preferred split gate flash EPROM cell or the dual gate flash EPROM cell consists of p<+>-doped semiconductor material so that a very good difference threshold ratio can be expected from the fully depleted cylinder.

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